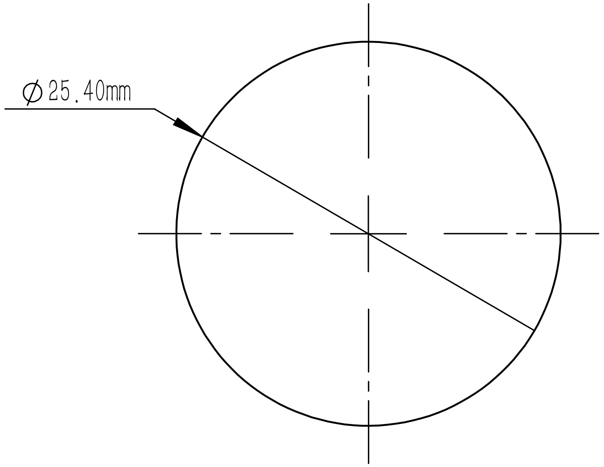

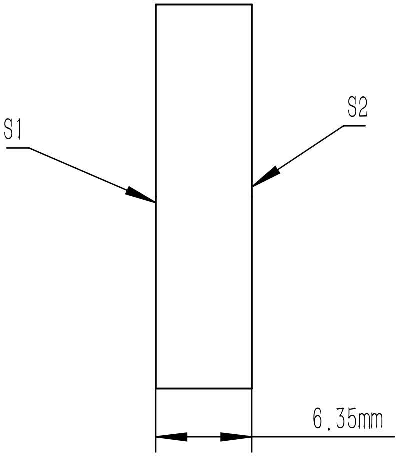

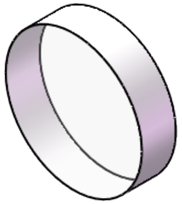

NOTES:

1. MATERIAL: UVFS
2. OPERATION WAVELENGTH: 532 nm
3. CLEAR APERTURE: >90%CA
4. SURFACE QUALITY (S1,S2): 20/10 (S/D)
5. SURFACE FLATNESS (S1,S2): λ/10@632.8 nm
6. PARALLELISM (S1,S2): <5 arcsec
7. CHAMFER: <0.2 mm, 45°
8. COATING (S1): HIGH ENERGY LASER LINE COATING
   R>99.8@532 nm, AOI=45°
9. DAMAGE THRESHOLD: >0.03MW/cm^2 CW

DRAWING PROJECTION			LBTEK			
	NAME	DATE	LPM10-532-HP-SP			
DRAWN	LTAN	Dec./21st/25	HIGH ENERGY LASER LINE MIRROR ⌀25.4 mm×6.35 mm,532 nm			
APPROVAL	WZCHENG	Dec./21st/25	MATERIAL	WEIGHT	SCALE	REV
FOR INFORMATION ONLY NOT FOR MANUFACTURING PURPOSES			UVFS	3.22 g	2:1	A